

Features

Advanced Trench MOS Technology
100% EAS Guaranteed
High Current Capability
Green Device Available

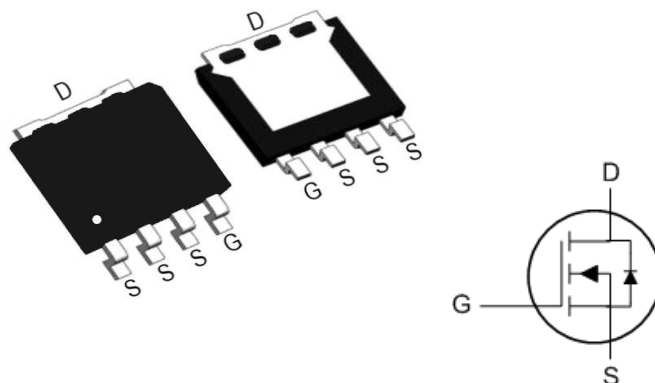
Product Summary

BVDSS	RDSON	ID
30V	0.5mΩ	387A

Applications

Power Management in Desktop Computer
DC/DC Converters

LPAK5X6 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	387	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	245	A
$I_D@T_A=25^{\circ}C$	Continuous Drain Current ¹	52	A
$I_D@T_A=70^{\circ}C$	Continuous Drain Current ¹	41	A
$I_D@T_A=100^{\circ}C$	Continuous Drain Current ¹	33	A
I_{DM}	Pulsed Drain Current ²	600	A
EAS	Single Pulse Avalanche Energy ³	125	mJ
I_{AS}	Avalanche Current	50	A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation ⁴	139	W
$P_D@T_A=25^{\circ}C$	Total Power Dissipation ⁴	2.5	W
T_{STG}	Storage Temperature Range	-55 to 150	$^{\circ}C$
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	50	$^{\circ}C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	0.9	$^{\circ}C/W$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	30	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=30A$	---	0.35	0.5	$m\Omega$
		$V_{GS}=4.5V$, $I_D=30A$	---	0.60	0.8	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1.2	1.7	2.2	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=24V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=24V$, $V_{GS}=0V$, $T_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	2.5	---	Ω
Q_g	Total Gate Charge (10V)	$V_{DS}=15V$, $V_{GS}=10V$, $I_D=30A$	---	157	---	nC
Q_g	Total Gate Charge (4.5V)		---	80	---	
Q_{gs}	Gate-Source Charge		---	25.8	---	
Q_{gd}	Gate-Drain Charge		---	29.8	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=20V$, $V_{GS}=10V$, $R_G=3\Omega$, $I_D=30A$	---	15.5	---	ns
T_r	Rise Time		---	58	---	
$T_{d(off)}$	Turn-Off Delay Time		---	130	---	
T_f	Fall Time		---	116	---	
C_{iss}	Input Capacitance	$V_{DS}=15V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	8983	---	pF
C_{oss}	Output Capacitance		---	3980	---	
C_{rss}	Reverse Transfer Capacitance		---	725	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,6}	$V_G=V_D=0V$, Force Current	---	---	100	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=1A$, $T_J=25^\circ\text{C}$	---	---	1.2	V
t_{rr}	Reverse Recovery Time	$I_F=30A$, $di/dt=100A/\mu s$, $T_J=25^\circ\text{C}$	---	104	---	nS
Q_{rr}	Reverse Recovery Charge		---	184	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V$, $V_{GS}=10V$, $L=0.1mH$, $I_{AS}=50A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.
- 6.Package limitation current is 100A.

Typical Characteristics

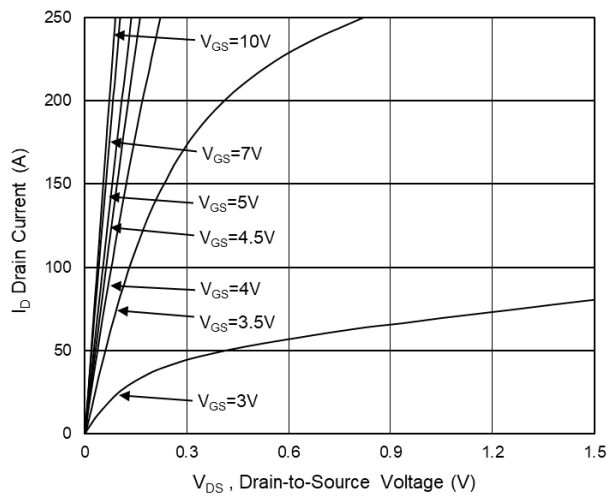


Fig.1 Typical Output Characteristics

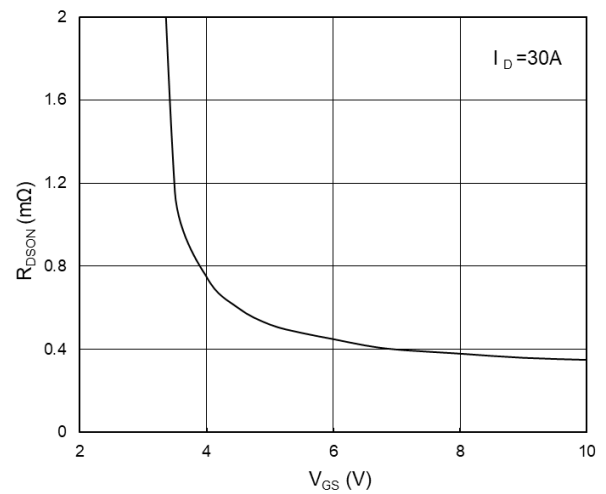


Fig.2 On-Resistance vs G-S Voltage

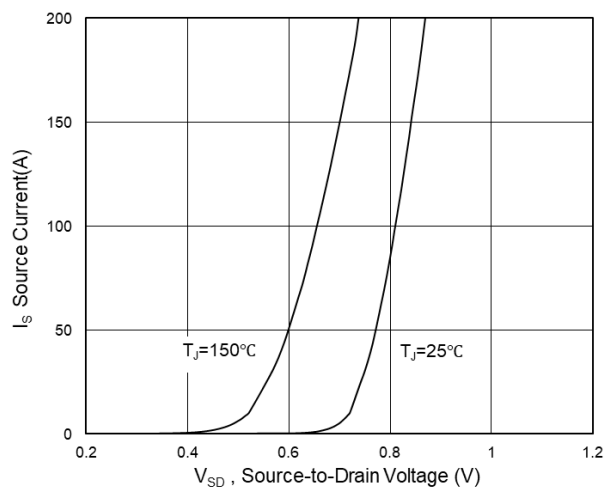


Fig.3 Source Drain Forward Characteristics

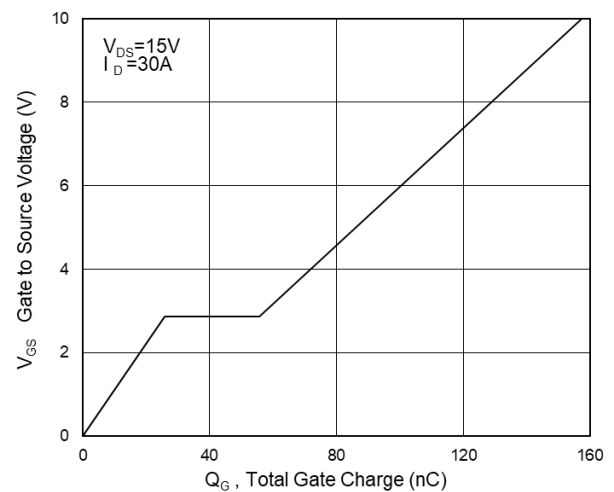


Fig.4 Gate-Charge Characteristics

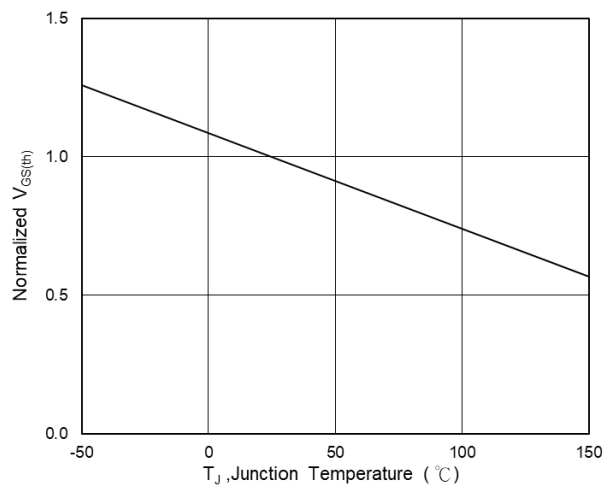


Fig.5 Normalized $V_{GS(th)}$ vs T_J

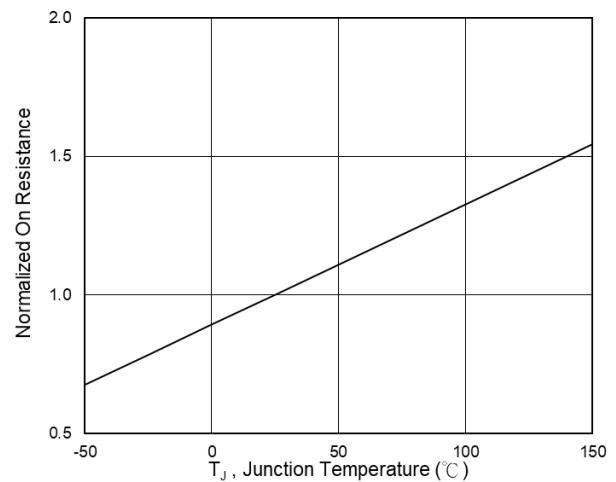


Fig.6 Normalized $R_{DS(on)}$ vs T_J

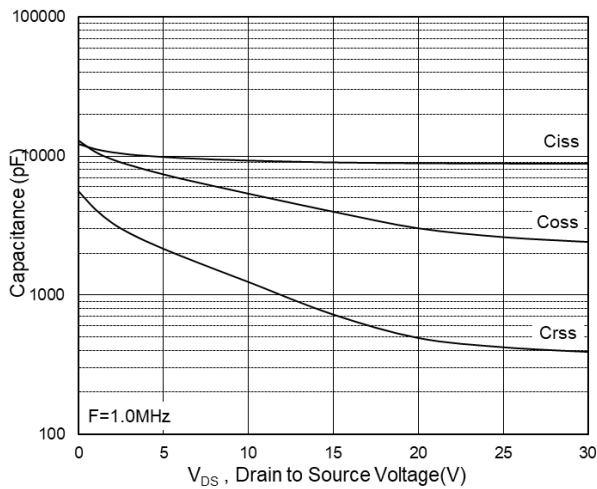


Fig.7 Capacitance

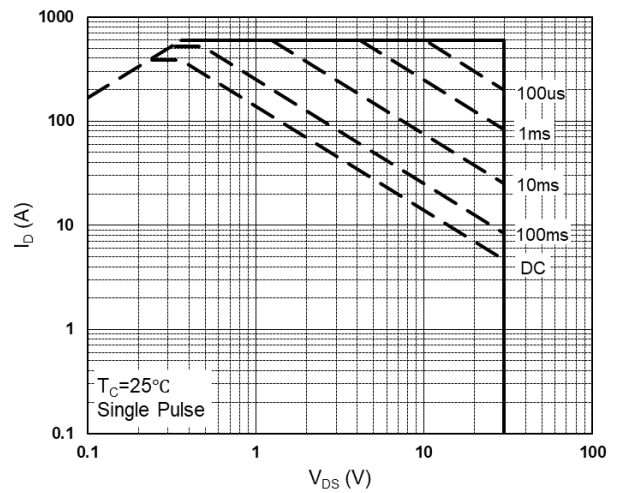


Fig.8 Safe Operating Area

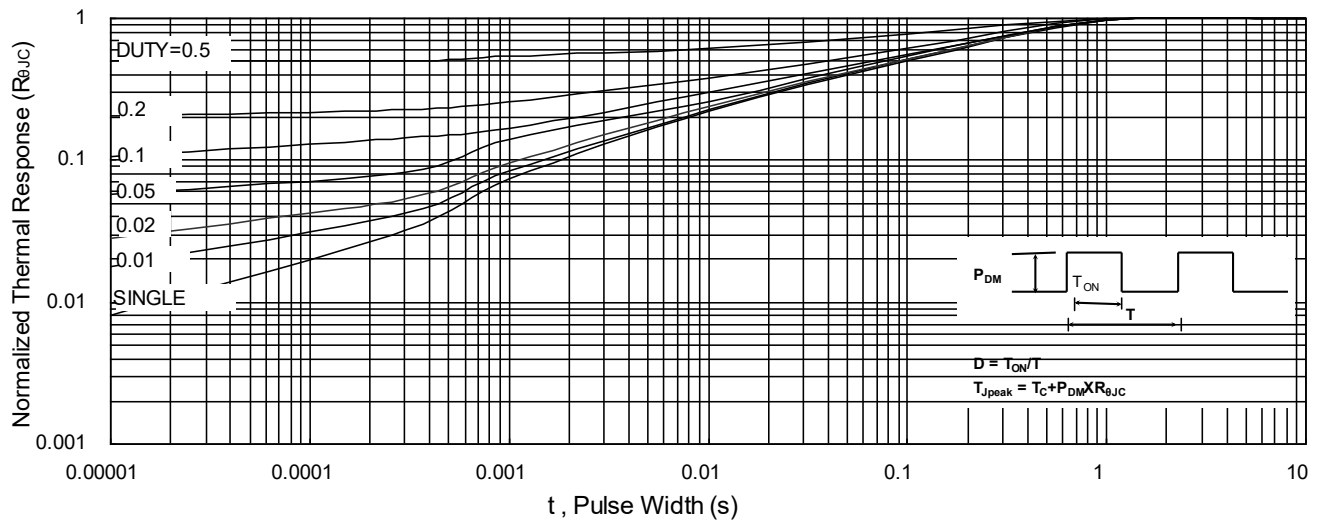
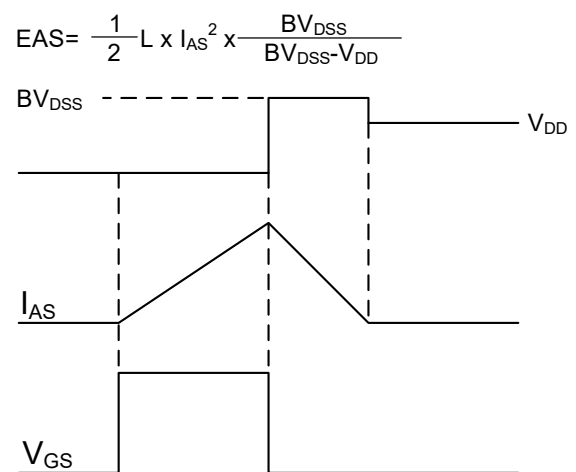
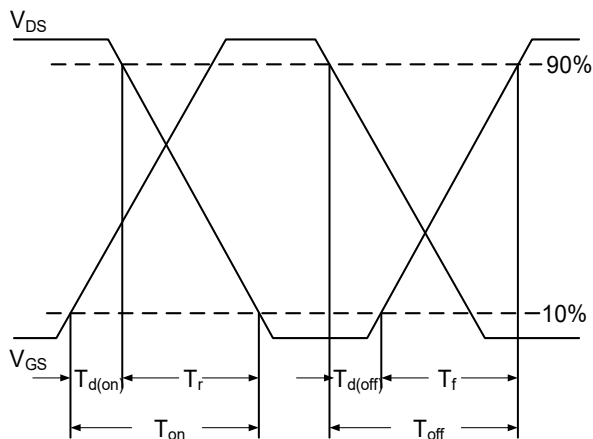


Fig.9 Normalized Maximum Transient Thermal Impedance



$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$

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